

Session 306: Future of Phase Change Memory

Altera

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Agenda

- Current State
- Value Proposition
- Technology Ramp Model
- Adoption Barriers

Phase Change Memory (PCM) Overview

| | DRAM | PCM | NAND Flash |
|--------------------|---------------|---------------------|-------------------|
| Read energy | 0.8 J/GB | 1 J/GB | 1.5 J/GB [28] |
| Write energy | 1.2 J/GB | 6 J/GB | 17.5 J/GB [28] |
| Idle power | ~100 mW/GB | ~1 mW/GB | 1–10 mW/GB |
| Endurance | ∞ | $10^6 - 10^8$ | $10^4 - 10^5$ |
| Page size | 64B | 64B | 4KB |
| Page read latency | 20-50ns | ~ 50ns | ~ 25 μ s |
| Page write latency | 20-50ns | ~ 1 μ s | ~ 500 μ s |
| Write bandwidth | ~GB/s per die | 50-100 MB/s per die | 5-40 MB/s per die |
| Erase latency | N/A | N/A | ~ 2 ms |
| Density | 1x | 2 – 4x | 4x |

Source: Chen, Gibbons, Nath, CIDR '11, Intel, Microsoft

- Reads close to DRAM
- Write latency 10X+ worse
 - But 100X+ better than NAND flash
- 100X+ better endurance
- Low idle power vs. DRAM

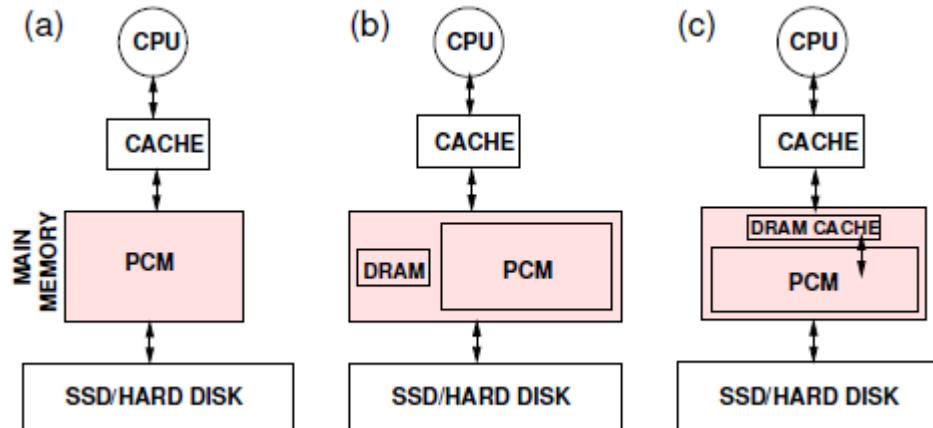
Value Proposition

- Lower Idle Power: for mobile
- Hybrid Enterprise Flash Cache Controller
- System Memory Hierarchy
- Flash Cache Endurance for Enterprise:
 - Better endurance for high IOPS environments
 - MLC NAND endurance getting worse in new process geometries

Hybrid Enterprise Flash Cache Controller PCM and NAND

- PCM for Metadata/logs
 - Block table
 - Partial writes
 - Garbage collection
 - Hot data tagging
- PCM for RAID parity
 - Fast
 - Less ECC
 - Better endurance
- PCM write thru cache

System Memory Hierarchy



Source: Chen, Gibbons, Nath, CIDR '11, Intel, Microsoft

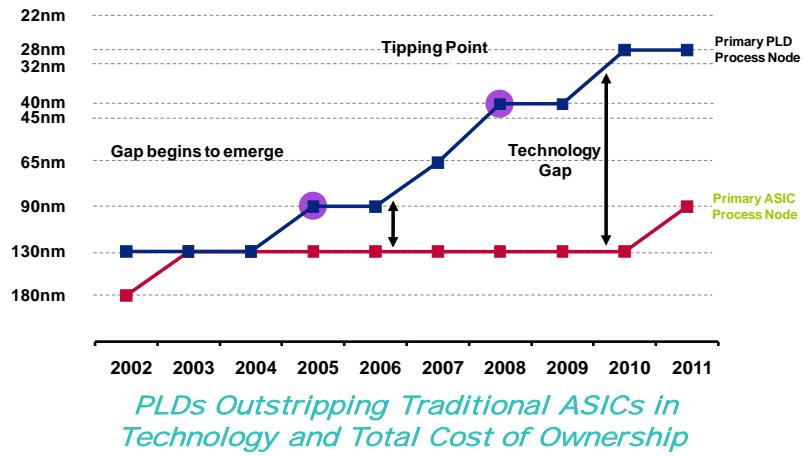
- O/S is DRAM aware: (b)
 - Also “storage class memory”
 - Application written to take advantage of it
- DRAM cache hidden: (c)

Technology Ramp

- Today: mobile
- Shorter term:
 - Customer prototyping within a year
 - Hybrid enterprise flash cache controllers
 - High transaction rate enterprise flash cache
- Longer term:
 - General enterprise flash cache replacement
 - Applications which are DRAM and PCM aware

Adoption Barriers

- Fast innovation
 - Hybrid controller algorithms
 - What is hot, what goes where
 - Partial writes, write thru, ...
- Uncertain forecast
- Need fast TTM
- Differentiation
 - Dedupe, hybrid algorithms, etc.
- High ASIC dev. costs
 - Increasing technology gap
 - vs. FPGA
 - 8G SerDes PHY
 - Usually on 40 nm
 - PCIe Gen3, 12G SAS



Thank You